

# Supporting Information

## Improved Sensitivity in Schottky Contacted Two-dimensional MoS<sub>2</sub> Gas Sensor

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#### A. CVD MoS<sub>2</sub> process temperature

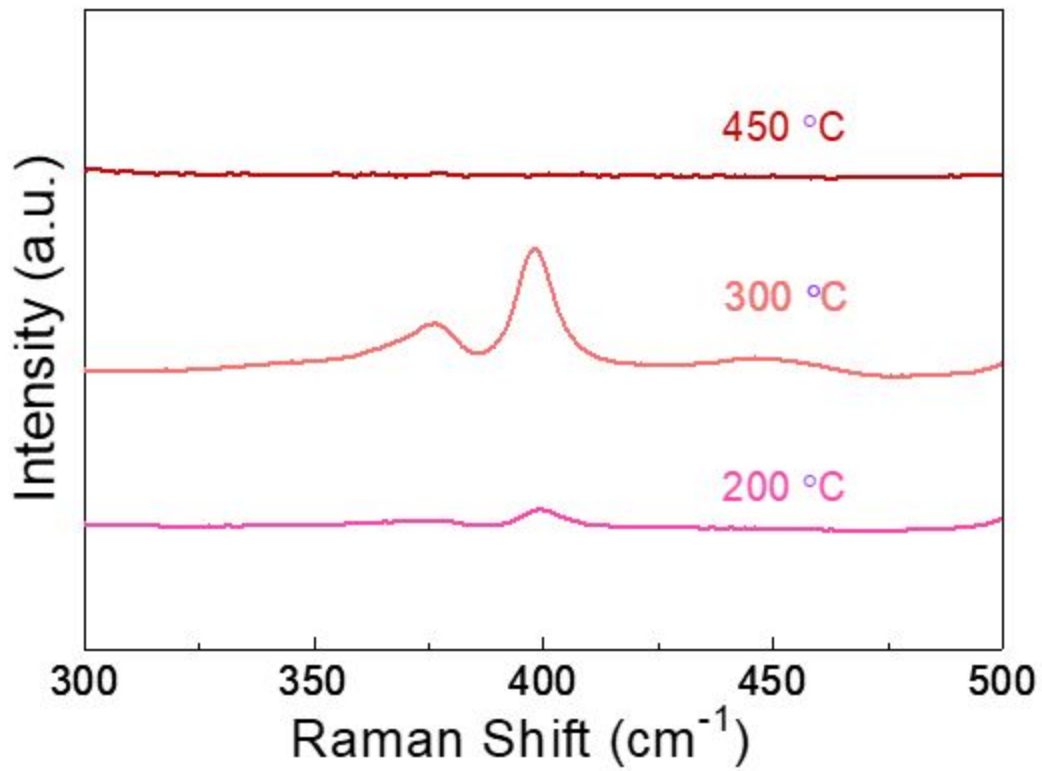
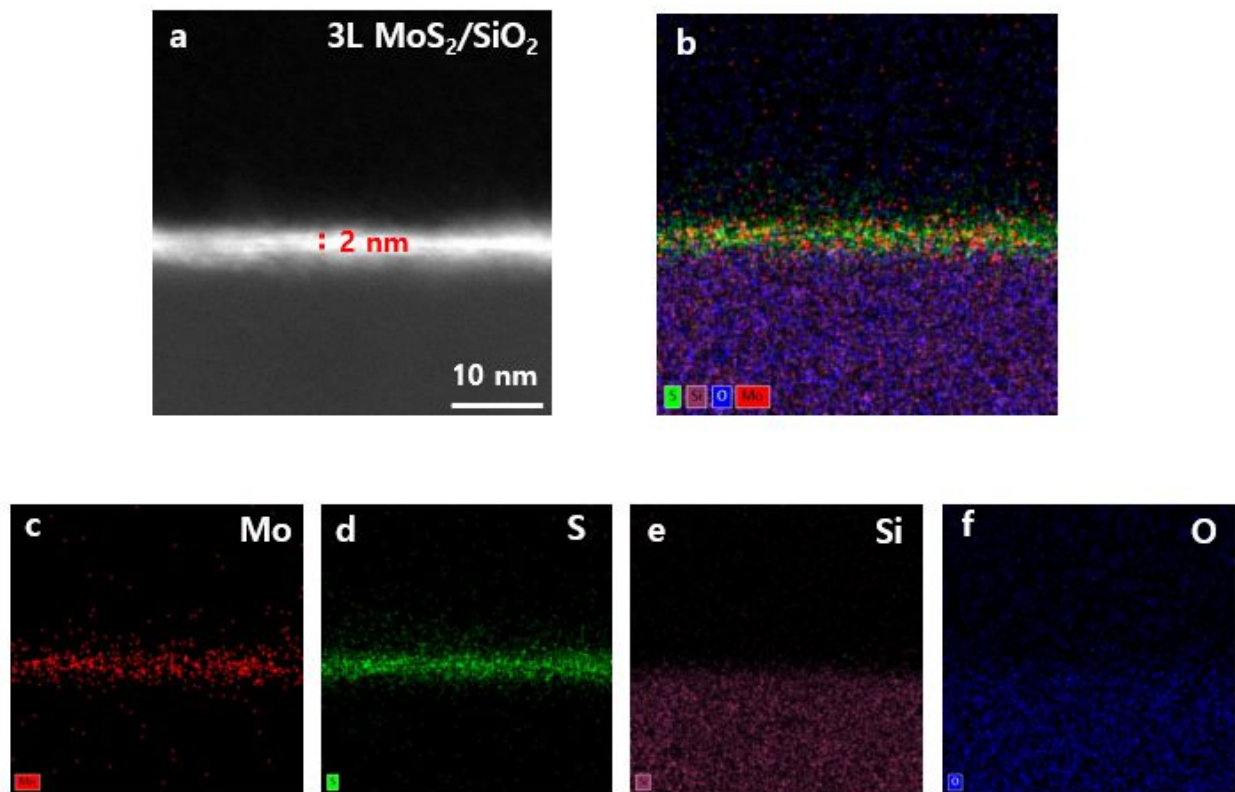


Figure. S1 Raman spectra of the MoS<sub>2</sub> at different CVD process temperatures.

## B. Characterization 3L MoS<sub>2</sub> on SiO<sub>2</sub>



**Figure S2** (a) High-angle annular dark-field (HAADF) image of 3L MoS<sub>2</sub> EDS mapping of 3L MoS<sub>2</sub> (b), Mo atoms (c), S atoms (d), Si atoms (e), and O atoms (f).